

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s)	Katsumi Sameshima	Examiner:	Wai-Sing Louie
Serial No.:	09/451,979	Group Art Unit:	2814
Confirmation No.:	Unassigned	Docket:	362-39
Filed:	November 30, 1999	Dated:	August 9, 2001
For:	FERROELECTRIC MEMORY AND METHOD FOR MANUFACTURING SAME		

Commissioner for Patents
Washington, DC 20231

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20231 on August 9, 2001

Signature: _____

Jayce Peterson

AMENDMENT

Sir:

In response to the non-final Office Action mailed May 9, 2001, a reply to which is due August 9, 2001, please amend the above-identified application in accordance with 37 C.F.R. §1.121 as follows:

IN THE SPECIFICATION:

At page 1, replace the paragraph beginning at line 25 and ending at page 2, line 9 with the following:

In the prior art, however, a conductive film 5a, a ferroelectric film 4a and a conductive film 3a are formed to a thickness to provide an upper electrode 5, a ferroelectric film 4 and a lower electrode 3, so that dry etching is then conducted throughout a total film thickness in order to remove unwanted portions of these films. Thus, the prior art has required a much greater etch amount and hence a longer etch time. This results in longer